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a gate electrode formed on the insulating gate film, and provided with a first region including a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the insulating gate film via the first region, the first and second regions having an identical conductivity type.

4. (Five Times Amended) A semiconductor device comprising:

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an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes, a channel forming region provided between the pair of main electrodes, an insulating gate film formed on the channel forming region, and a gate electrode formed on the insulating gate film, and provided with a first region including a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the insulating gate film via the first region, the first and second regions having an identical conductivity type; and

a silicide electrode formed in contact with the second region of the gate electrode, and being substantially free from the second group IV element.

11. (Five Times Amended) A semiconductor device comprising:

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an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes, a channel forming region provided between the pair of main electrodes, an insulating gate film formed on the channel forming region, and a gate electrode formed on the insulating gate film, and provided with a first region including a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including a multiple element compound including the first and second group IV elements and metal, and formed on the insulating gate film via the first region, the first and second regions having an identical conductivity type; and

a silicide electrode formed in contact with the second region of the gate electrode, including the first group IV element and metal, and being substantially free from the second group IV element.

f4 15. (Four Times Amended) A semiconductor device comprising:
a semiconductor region of a first conductivity type;
an epitaxial growth layer formed on the semiconductor region and having a first region of the first conductivity type including a first group IV element and a second group IV element and formed in contact with the semiconductor region, and a second region of the first conductivity type including the first group IV element and formed on the semiconductor region via the first region; and
a silicide electrode formed on the second region of the epitaxial growth layer.

f5 23. (Five Times Amended) A semiconductor device comprising:
an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes, a channel forming region provided between the pair of main electrodes, an insulating gate film formed on the channel forming region, and a gate electrode formed on the insulating gate film, and provided with a first region including a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the insulating gate film via the first region, the first and second regions having an identical conductivity type;
an elevated electrode formed on the main electrodes, and having a third region including a third group IV element and a fourth group IV element and a fourth region formed on the main electrode via the third region and including the third group IV element;
a first silicide electrode formed in contact with the second region of the gate electrode, and being substantially free from the second group IV element; and
a second silicide electrode formed in contact with the fourth region of the elevated electrode, and being substantially free from the fourth group IV element.

f6 32. (Amended) A semiconductor device comprising:
a first conductivity type insulated gate field effect transistor having a pair of first conductivity type main electrodes used as source and drain electrodes, a second conductivity type channel forming region provided between the pair of first conductivity type main electrodes, a first insulating gate film formed on the second conductivity type channel

forming region, and a first gate electrode formed on the first insulating gate film, and provided with a first region including a first group IV element and a second group IV element and formed in contact with the first insulating gate film, and a second region including the first group IV element and formed on the first insulating gate film via the first region, the first and second regions having an identical conductivity type; and

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a second conductivity type insulated gate field effect transistor having a pair of second conductivity type main electrodes used as source and drain electrodes, a first conductivity type channel forming region provided between the pair of second conductivity type main electrodes, a second insulating gate film formed on the first conductivity type channel forming region, and a second gate electrode formed on the second insulating gate film, and provided with a third region including the first group IV element and the second group IV element and formed in contact with the second insulating gate film, and a fourth region including the first group IV element and formed on the second insulating gate film via the third region, the third and fourth regions having the identical conductivity type.

33. (Amended) A semiconductor device comprising:

an insulated gate field effect transistor having a pair of main electrodes used as source and drain electrodes, a channel forming region provided between the pair of main electrodes, an insulating gate film formed on the channel forming region, and a gate electrode formed on the insulating gate film, and provided with a first region including a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the insulating gate film via the first region, the first and second regions having an identical conductivity type; and

an element isolation region formed surrounding the insulated gate field effect transistor, and having an insulating film embedded in a trench.

Please add the following new claims 34 and 35:

34. (New) A semiconductor device comprising:

a pair of main electrodes used as source and drain electrodes;
a channel forming region provided between the pair of main electrodes;

an insulating gate film formed on the channel forming region; and
a gate electrode formed on the insulating gate film, and provided with a first region including a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the first region, the first and second regions having an identical conductivity type, and being formed on the same side of the insulating gate film.

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35. (New) A semiconductor device comprising:
a semiconductor substrate;
a well region formed on the main surface of the semiconductor substrate;
a pair of main electrodes used as source and drain electrodes formed on the main surface of the well region;
a channel forming region provided between the pair of main electrodes in the well region;
an insulating gate film formed on the channel forming region; and
a gate electrode formed on the insulating gate film, and provided with a first region including a first group IV element and a second group IV element and formed in contact with the insulating gate film, and a second region including the first group IV element and formed on the insulating gate film via the first region, the first and second regions having an identical conductivity type.
